

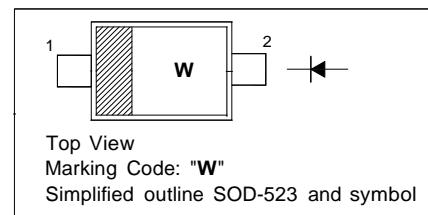
Silicon Schottky Barrier Diode

Features

- Low reverse current
- Ultra small flat package is suitable for surface mount design

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	25	V
Forward Current	I_F	50	mA
Non-Repetitive Peak Forward Surge Current	I_{FSM}	200	mA
Junction Temperature Range	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 5\text{ mA}$	V_F	0.33 0.38	V
Reverse Current at $V_R = 20\text{ V}$	I_R	0.45	μA
Junction Capacitance at $V_R = 1\text{ V}$, $f = 1\text{ MHz}$	C_J	20	pF

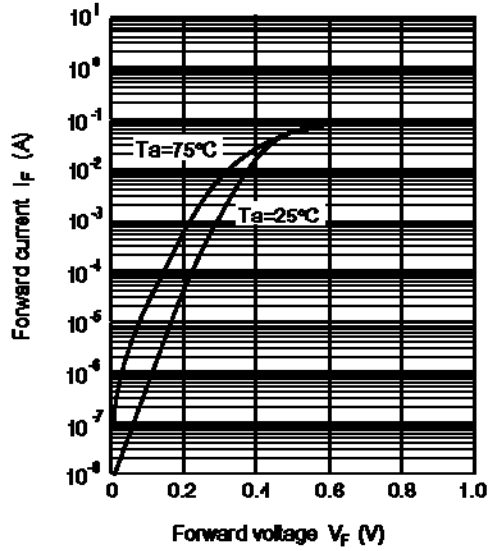


Fig.1 Forward current Vs. Forward voltage

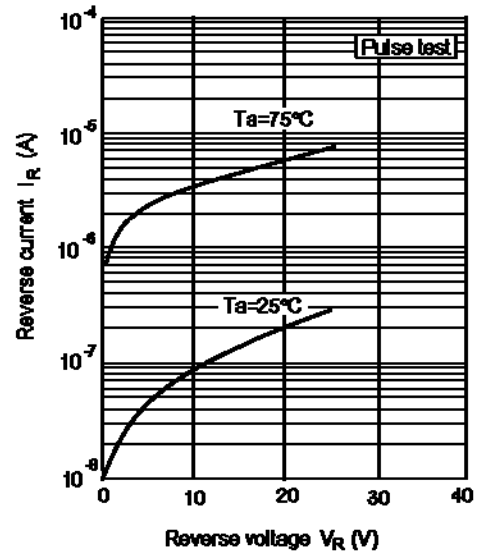
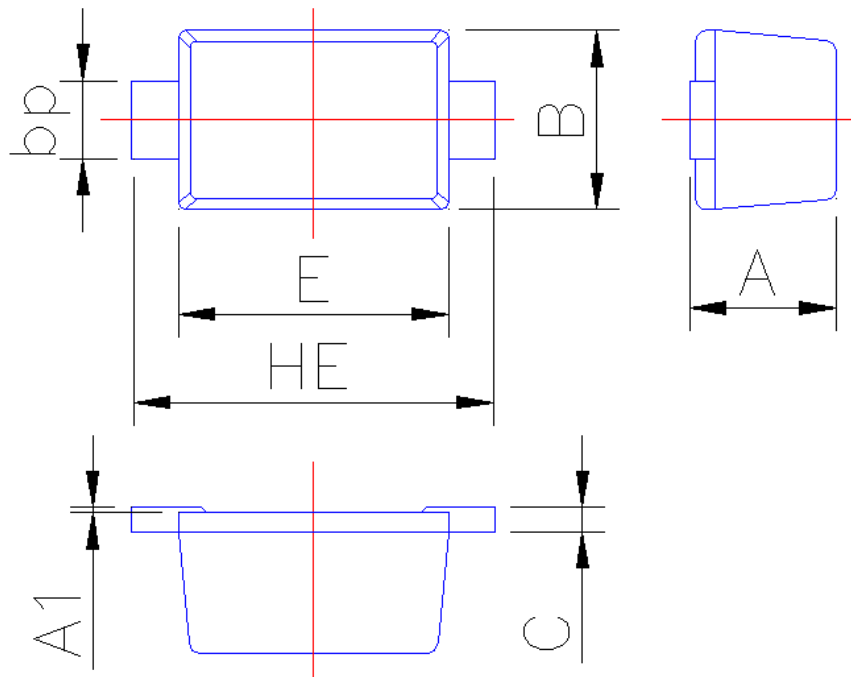


Fig.2 Reverse current Vs. Reverse voltage

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



Symbol	Dimension in Millimeters	
	Min	Max
A	0.60	0.70
A1	0	0.05
B	0.75	0.85
bp	0.25	0.40
C	0.09	0.15
E	1.15	1.25
HE	1.50	1.70